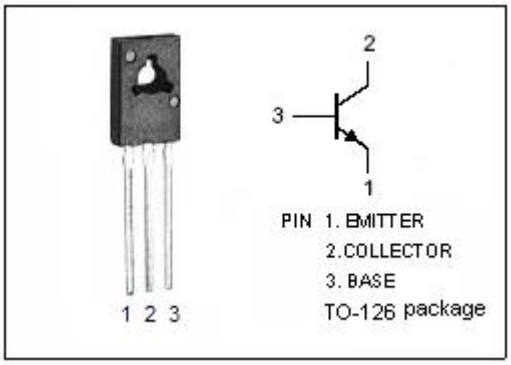
isc Silicon NPN Power Transistor — 2SC2258

DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 250V(Min)
- High Current-Gain Bandwidth Product
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

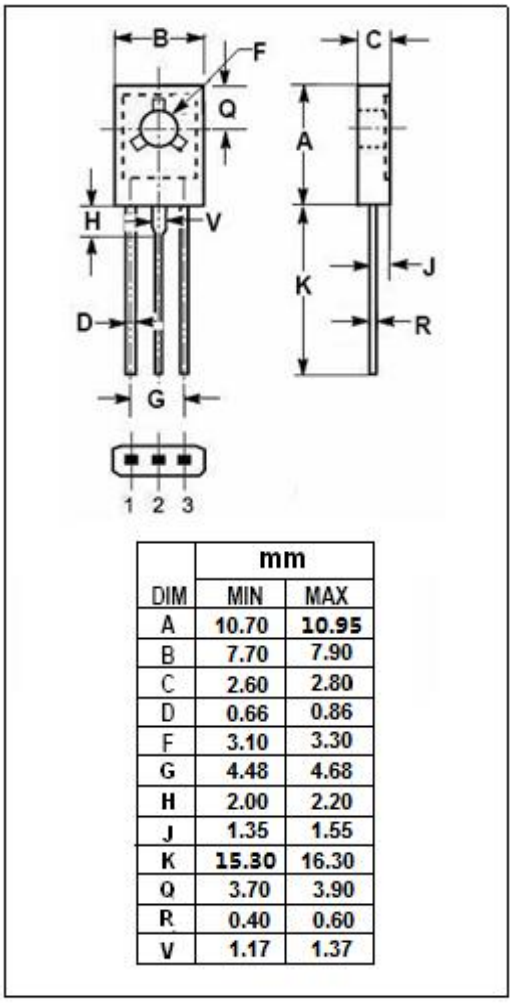


APPLICATIONS

- For high breakdown voltage general amplification
- For video output amplification

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	250	V
V_{CEO}	Collector-Emitter Voltage	250	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	0.1	A
I_{CM}	Collector Current-Peak	0.15	A
P_C	Collector Power Dissipation @ T_C=25℃	4	W
	Collector Power Dissipation @ T_a=25℃	1.2	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-Base Breakdown Vltage	I_E= 0.1mA ; I_C= 0	7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 50mA; I_B=5mA			1.2	V
$V_{BE(on)}$	Collector-Emitter On Voltage	I_C= 40mA ; V_{CE}= 20V			1.2	V
I_{CER}	Collector Cutoff Current	V_{CE}= 250V; R_{BE}= 100kΩ			100	μA
h_{FE-1}	DC Current Gain	I_C= 40mA ; V_{CE}= 20V	40			
h_{FE-2}	DC Current Gain	I_C= 5mA ; V_{CE}= 50V	30			
f_T	Current-Gain—Bandwidth Product	I_E= -10mA;V_{CB}= 10V;f_{test}= 200MHz		100		MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 50V,f_{test}= 1MHz		3		pF